differently, the semiconductor device 1, 11 may not be a packaged type. In addition, the semiconductor device 1, 11 may not be of a flipped-chip mounting type.

Only two factors need to be considered in determining to what extent the chip 2 is to be thinned down: the resultant chip 2 should receive a predetermined stress so that is deforms sufficiently when detached from the board 3; and the functions of the transistor, LSI circuit, and other components on the chip 2 should not be adversely affected when the chip 2 is level. Accordingly, there are no particular limitations on the thickness of the chip 2.

However, specifically, in view of the strength of silicon, the chip preferably has a thickness of 50 μm or less and more preferably in a range of 30 μm to 50 μm.

If being thinned down in this range, the chip 2 can avoid adversely affecting the functions of the transistor, LSI circuit, and other components when it is level, as well as can deform (e.g., warp) surely as desired when detached from the board 3.

As shown in Figure 2, the sensor section 22 in the chip 2 is preferably interposed at least between the transistor section 21 and the LSI circuit section 23. This is because, as described earlier, the detector section is provided in the sensor section 22 so as to

electrically connect the transistor to the LSI circuit.

However, the sensor section 22 is not necessarily positioned between the transistor section 21 and the LSI circuit section 23, and may be positioned anywhere as long as it can electrically connect the transistor section 21 to the LSI circuit section 23. Accordingly, there is no particular limitations on the relative positions of the transistor section 21, sensor section 22, and LSI circuit section 23.

The LSI circuit 26 shown in Figure 3 includes an operation prohibition circuit 27 which allows the LSI circuit 26 to operate only when it receives low signal from the distortion sensor 25. Accordingly, the operation prohibition circuit 27 has a function of prohibiting the LSI circuit 26 from operating when the LSI circuit 26 alone is subjected to probing for circuit analysis.

Further, the operation prohibition circuit 27 only needs to be arranged to have the foregoing function and is not limited in any particular manner. The operation prohibition circuit 27 can be assembled from a resistor, for example. Alternatively, the operation prohibition circuit 27 may be arranged so that the power source and grounding of the distortion sensor 25 are provided at a common pad with the LSI circuit 26.

The distortion sensor 25 is not limited only to the

arrangement shown in Figure 3. The distortion sensor 25 only needs to be arranged to be capable of detecting changes in value of the characteristic current I_d of the transistor 24 caused by the deformation of the level transistor section 21.

Specifically, for example, as the distortion sensor, an arrangement may be employed which, upon detection of a characteristic current of a predetermined value (or in a predetermined range), supplies such a signal (operation signal) to the LSI circuit that causes the LSI circuit to operate normally. Upon detection of a characteristic current of a value not equal to the predetermined value (or out of the predetermined range) or failure to detect the characteristic current, this distortion sensor preferably supplies such a signal (operation prohibit signal) to the LSI circuit that stops (prohibits) the operation of the LSI circuit. Another preferred arrangement is to stop the supply of the operation signal.

If the stress-induced deformation of the chip causes a change in an electrical property in any part of the chip other than the transistor section, a distortion sensor capable of detecting this change may be used as detector means. In this event, the distortion sensor is preferably arranged to detect a change in an electrical

property occurring in that part and supplies a signal to the LSI circuit to prohibit the LSI circuit from operating.

In this manner, if such a part exists, the transistor section is not the only part which deforms due to stress (in which an electrical property changes) in the chip. In addition, the distortion sensor (detector section) may be positioned somewhere other than in the sensor section.

[Embodiment 3]

A third embodiment in accordance with the present invention will be now described. Here, for convenience, members of the present embodiment that have the same function as members of either of the first and second embodiments, and that are mentioned in that embodiment are indicated by the same reference numerals and description thereof is omitted.

Figure 10(a) is an explanatory drawing showing an arrangement of a semiconductor device 30 of the present embodiment. As shown in this Figure, the semiconductor device 30 is of a packaged type including a silicon semiconductor element chip (semiconductor element; hereinafter, simply "chip") 31 sealed inside an epoxy resin package 37.

The chip 31 is secured onto a die pad (board) 32 interposed by a silver paste 33.

On the front of the chip 31 are there provided an electronic circuit section and a pad section 35 as will be described later in detail. The pad section 35 is electrically connected to a lead wire 36 via a gold wire 34. In this manner, the semiconductor device 30 has a structure of a wire bonding type.

The back 31a of the chip 31 is subjected to rough surface processing to provide stress to the chip 31. As a result of the rough surface processing, the chip 31 (especially, the processed part) warps convexly due to stress when removed from the package 37 (detached from the die pad 32) as shown in Figure 10(b).

The chip 31 has thickness of 200 μm or more, whereas the part subjected to the rough surface processing is thinned down to 50 μm or less, and preferably in a range of 30 μm to 50 μm. Accordingly, the chip 31 (especially, the processing part) readily deforms due to stress when detached from the die pad 32.

The electronic circuit section provided on the front of the chip 31 includes a transistor section, a sensor section, and an LSI circuit section similarly to the electronic circuit section on the chip 2 shown in Figure 2.

The transistor section is a part where transistors are provided at high density. The sensor section is a part where a detector section (detector means) is provided together with a comparator and other components so as to detect an electrical property of the transistors. The LSI circuit section is a part where circuitry including an IC (integrated circuit) or LSI (large-scale integration) circuit is provided.

Especially, the electronic circuit section (at least the transistor section) is provided where the chip 31 is thinned down.

Now, a method of manufacturing the semiconductor device 30 will be described as an example.

First, a lead frame 38 is fabricated including a die pad 32 and a lead wire 36 at positions that match the mounting position of the chip 31.

A part of the die pad 32 is omitted to make a hollow space. Consequently, as shown in Figure 11, the die pad 32 has a hollow section 32a to allow internal access during the processing carried out in a later step on at least a part of the back 31a of the chip 31.

Next, as shown in Figure 12, silver paste 33 is applied onto the die pad 32. The chip 31 is then placed on the die pad 32 while positioning correctly. The die pad 32 and chip 31 are compressed and secured to each

other, while heating at about 160 °C to 170 °C. The silver paste 33 solidifies due to the heating, securing the chip 31 onto the die pad 32.

The pad section 35 of the chip 31 is electrically connected (wire bonded) to the lead wire 36 by the gold wire 34. Thereafter, a part of the package 37 is formed using a predetermined mold, by sealing with epoxy resin the die pad 32 except the hollow section 32a, i.e., the chip 31 except a part of the back 31a to be processed.

Then, the chip 31 thus secured and sealed is loaded in a predetermined place of a dicing machine. The back 31a of the chip 31 is scraped using a dicing blade provided in the dicing machine as shown in Figure 13. The scraping is carried out to reduce the thickness of the chip 31 to 50 μm or less, preferably to a range of 30 μm to 50 μm. There are no particular requirements for the scraping.

Such scrape processing, that is, the provision of a rough surface and reduction in thickness of a part of the back 31a of the chip 31 enables a predetermined stress to be applied to the chip 31 (especially, the processed part).

Then, as shown in Figure 14, the back 31a of the processed chip 31 is sealed with epoxy resin using a predetermined mold to fabricate the package 37, which

completes the manufacture of the semiconductor device 30.

In this manner, the chip 31 has its back 31a subjected to rough surface processing. Therefore, once detached from the die pad 32 and deformed by stress, the chip 31 never completely returns to the level shape even by, for example, vacuum adsorption on a level base. To put it differently, the chip 31, once deformed, by no means completely returns to the level shape. Nor can any analysis be conducted on the LSI and other circuits, once the chip 31 is deformed, as described in the first embodiment.

Specifically, if the package 37 is removed from the chip 31 followed by detachment of the chip 31 from the die pad 32, the chip 31 (especially, transistor section) warps convexly due to stress. The warp causes a property of the transistor section to change, increasing its characteristic current I_d in value. Consequently, the characteristic voltage V_1 grows larger than the predetermined voltage V_2 ($V_1 > V_2$).

Therefore, the comparator Cp in the sensor section outputs high signal to the LSI circuit in the LSI circuit section, causing the operation prohibition circuit 27 to stop the operation of the LSI circuit. In these conditions, an attempt to conduct probing on the LSI circuit through application of drive voltage to the

transistor 24 does not result in a successful circuit analysis.

Note that the chip 31 is scraped after sealed with epoxy resin. Therefore, the chip 31 can retain its level shape inside the semiconductor device 30 even when it is thinned down and receives stress.

As can be seen from Figure 15 and Figure 16, in a conventional semiconductor device in which a die pad 42 without a hollow section, the back of the chip 31 cannot be subjected to processing after the chip 31 is secure. By contrast, in the semiconductor device 30, the die pad 32 to which the chip 31 is secured has a hollow section 32a which offers access to the back 31a of the chip 31 for processing after the chip 31 is secured.

Throughout the first to third embodiments, the chip 2, 12, and 31 (transistor section 21) have been described to warp convexly. However, this is not the only possibility. Alternatively, after the chip may be subjected to such processing that the chip deforms and takes a different shape (for example, concavely) when detached from the board.

Further, throughout the first to third embodiments, the transistor in the transistor section 21 are of an NMOS type (N-type metal oxide semiconductor). However, the transistor in the transistor section 21 is not

limited to an NMOS type, as long as its electrical property (e.g., characteristic current I_d) changes when the transistor section 21 deforms. Similarly, there are no particular limitations on the specific arrangement of the circuit provided in the LSI circuit section 23.

For example, the transistor section 21 may include a transistor of a PMOS type (P-type metal oxide semiconductor).

With a PMOS transistor, the value of the characteristic current I_d changes oppositely; therefore, for example, by setting the reference oppositely for the comparator Cp, an identical effect is produced with an NMOS transistor.

Specifically, when the PMOS transistor is used, a stress (external force) is applied to the transistor section 21 so that it warps convexly in a direction perpendicular to current flow through the transistor and normal to the front of the chip 2, and as a result, the transistor section 21 actually warps due to the stress, forming a warped surface having a radius (r) of 10 mm. In these circumstances, the transistor, when activated, shows a 10 % decrease in its channel current.

If the semiconductor device is not of a flipped-chip mounting type, for example, the semiconductor element chip (semiconductor element) only needs to be covered all

over (including the board) with a single material. Alternatively, the back of the semiconductor element chip is covered with a material having a higher rate for etchant than that of the material covering the front of the semiconductor element chip.

In this alternative, if the front of the semiconductor element chip is to be exposed by etching, the etchant reaches and etches the back of the semiconductor element chip too, thereby forcing the semiconductor element chip to deform when detached.

There are no particular limitations on the material of the package 37, die pad 32, and other members of the third embodiment.

The third embodiment only refers to a case where the back 31a of the chip 31 is partially scraped by dicing; however, the back 31a of the chip 31 may be scraped by a method other than dicing.

Further, there are no particular limitations on which parts of the chip 31 is(are) to be thinned down. However, the chip 31 is preferably thinned down so that at least the transistor section deforms due to stress to enable the distortion sensor (detector section) to detect an electrical property of the transistor.

Now, a brief description will be given below why a back-scraped (treated) chip warps by taking a wafer

fabricated into chips as an example.

In manufacture of a semiconductor device, typically, a wafer made of chip base material (e.g., silicon) is polished and divided into a number of chips which are then packaged.

In the polishing, normally, a wafer is thinned down from its original thickness of 725 μm to about 200 μm to 300 μm, using grinding stone (#2000 to finish off the process).

Figure 17 is a graph showing measurements of relationships between the thickness and warp (degree of warp) of wafers which have been thinned down from their original thickness of 725 μm by polishing. Measurements were made on two round wafers (distinguished by ■ and ●) of 8 inches in diameter which had the same specifications.

A warp of the wafer is defined as the difference (distance) between the highest and lowest points on the wafer mounted on a flat plane. The round wafer warps like a dome, so the warp is defined as the difference between the center and edge.

As shown in the graph of Figure 17, as the polishing progresses and the wafer is thinned down, the wafer warps increasingly.

Figure 18 is a graph showing measurements of

relationships between amounts of etching and warp of wafers whose polished surfaces have been wet etched. Measurements were made on three wafers (distinguished by ◆, ■ and ●) which had the same specifications.

As shown in the graph of Figure 18, etching about 1 μm of the polished surface to form a mirror surface enables the warped wafer to revert to the original shape.

Considering the two graphs (data) in combination, it is understood that a stressed layer so thin (about 1 μm) as to be removable by etching is formed on the wafer by the polishing (scraping) and warps the wafer.

We assume that polishing (scraping) of the wafer results in formation of a stress layer for the following reasons.

A wafer made of semiconductor base material (chip base material, typically silicon) retains its normal state (non-stressed state) as long as the surface crystals are interconnected orderly. Polishing damages the wafer surface and breaks the connections linking crystals, disrupting the orderly crystalline structure. The part of the surface subjected to polishing and thereby undergoing disruption in the crystalline structure in this manner becomes a stressed (disrupted) layer.

Theoretically, the relationship between warp and

stress are given by

$$\sigma = (E \cdot h^2) \ / \ ((1-\upsilon) \cdot 6 \cdot Rt)$$

where $E/(1-\upsilon)$ is the elastic coefficient of the wafer in Pa, h is the thickness of the wafer, t is the thickness of the stressed layer, R is the radius of curvature matched to the warp of the wafer, and σ is the mean value of stress.

The radius of curvature matched to the warp decreases with an increase in the warp. Therefore, the above formula shows that the wafer warps in inverse proportion to the square of its thickness. This well coincides with the measurements shown in Figure 17 (there is only one variable parameter involved: the thickness of the wafer).

The present invention exploits this warping caused by the stressed layer, where the polishing (scraping) is carried out by scraping (processing) by means of dicing, sand blast, or sandpaper.

Scraping by means of dicing, sand blast, or sandpaper results in formation of a stressed layer similarly to the foregoing polishing and thereby causes the wafer to warp. If the chip is thinned down (less than or equal to 50 μm), the chip warps more readily. Laser treatment also produces a similar stressed layer.

As described so far, a semiconductor device in accordance with the present invention (the present semiconductor device) includes a semiconductor element secured to a board, including:

a detector section for detecting detachment of the semiconductor element from the board; and

an operation prohibition section for prohibiting operation of the semiconductor element when the detector section has detected the detachment of the semiconductor element from the board.

The present semiconductor device is arranged so that when the semiconductor element has been detached (or is to detached) from the board, the operation prohibition section causes the semiconductor element to be incapable of operating. Hence, with the present semiconductor device, the semiconductor element is specified to failed to operate normally once detached from the board.

This prevents anyone unrelated to the manufacture of the present semiconductor device from conducting detailed analysis on the semiconductor element and thereby ensures safe concealment of secrets about the semiconductor element (e.g., operational properties of the integrated circuit).

It is preferred in the present semiconductor device if the semiconductor element is specified to deform when

detached from the board and the detector section is specified to detect the detachment of the semiconductor element from the board through detection of the deformation of the semiconductor element. This allows the use of the distortion sensor as the detector section and facilitates the realization of the semiconductor device.

It is further preferred in this case if the semiconductor element includes a transistor having an electrical property changing according to the deformation of the semiconductor element and the detector section is specified to detect the deformation of the semiconductor element through detection of the change in the electrical property of the transistor.

The NMOS and PMOS transistors change electrical properties according to their deformation. Therefore, the deformation and detachment of the semiconductor element are detectable through detection of the change. This facilitates the provision of the present semiconductor device.

It is further preferred in this case if the detector section is specified to output an operation signal to the operation prohibition section when the electrical property of the transistor does not change and to stop the output of the operation signal when the electrical property of the transistor changes, and the operation

prohibition section is specified not to prohibit the operation of the semiconductor element only while receiving the operation signal. This enables the operation of the operation prohibition section to be readily controllable.

It is also preferred in the present semiconductor device either if both the detector section and the operation prohibition section are formed on the semiconductor element or if the operation prohibition section is formed on the semiconductor element. This enables the operation prohibition section to continue to be in control even after the semiconductor element is completely detached from the board and separated from the present semiconductor device.

To specify the semiconductor element to deform if it is detached from the board, such stress should be applied to the semiconductor element when it is secured to the board that could otherwise deform the semiconductor element. The stress is provided by subjecting the semiconductor element either partially or entirely to rough surface processing when it is secured to the board. To facilitate the deformation, it is preferred if the semiconductor element has a reduced thickness of 50 μm or less (preferably, 30 μm to 50 μm) where the semiconductor element is subjected to the rough surface processing.

To describe the present invention differently, the present invention, for example, relates to a semiconductor device which can prevent analysis of the properties of the semiconductor element and circuit by making use of a change or the like that occurs to an electrical property of the transistor, integrated circuit, etc. as a result of the semiconductor element warping or otherwise deforming when the semiconductor element is detached from the board, as well as a method of manufacturing such a semiconductor device.

The semiconductor device in accordance with the present invention may be such that the semiconductor element including an integrated circuit is secured level onto the board in, for example, a package and operates normally only when the semiconductor element is level. The semiconductor element is specified to be receiving a stress (static stress) as a result of processing carried out on at least a part of its back and, when detached from the board, at least partially deform due to the stress. Therefore, when the semiconductor element is detached from all the other members and is no longer capable of retain its level shape, it changes in electrical and other properties and fail to operate normally. The semiconductor device in accordance with the present invention is specified to prevent analysis of the

properties of the semiconductor element and circuit by making use of a change or the like that occurs to an electrical property of the transistor, integrated circuit, etc. as a result of the semiconductor element warping or otherwise deforming when the semiconductor element is detached from the board.

The chip 2 of Figures 1(a) and 1(b) may be secured via glue (anisotropic conducting glue) 5 onto a glass epoxy board (board) 3 formed by immersing, for example, epoxy resin in glass fiber. Since the bump 4 of the pad section 7 provided on the front of the chip 2 is connected to the wire section 6 made of copper film on the board 3, the semiconductor device 1 is of a flipped-chip mounting type.

The back 2a of the chip 2 may be subjected to predetermined processing and thereby entirely receives stress so that the chip 2 deforms when the chip 2 is removed from the package 8, that is, when the chip 2 is detached from the board 3.

The detector section in the sensor section 22 of Figure 2 may have a function of detecting a property of the transistor shown only when the transistor section 21 is level or an electrical property unique to a level part to control the operation of the LSI circuit in the LSI circuit section 23 and also a function of detecting a

change in electrical properties of the transistor section 21 when the transistor section 21 deforms (becomes no longer level) to stop controlling the operation of the LSI circuit in the LSI circuit section 23.

The distortion sensor 25 of Figure 3 is an example of an OP-amplifier as the detector means provided in the chip 2. The LSI circuit 26 of Figure 3 may include the operation prohibition circuit 27 for prohibiting the LSI circuit 26 from operating, so as not to operate unless it receives a signal from the comparator Cp. The provision of the operation prohibition circuit 27 prevents the LSI circuit 26 from operating unless the LSI circuit 26 receives a signal from the comparator Cp.

In the arrangement of Figure 3, when the transistor 24 receives a drive voltage, the characteristic voltage V_1 develops depending on the resistor R connected to the transistor 24 and the characteristic current I_d flowing through the transistor 24. The characteristic voltage V_1 is applied to one of the two input terminals of the comparator Cp. The comparator Cp compares the characteristic voltage V_1 with the predetermined voltage V_2 applied in advance to the other input terminal to determine which voltage is higher and outputs low signal from the output terminal to the LSI circuit 26 if the characteristic voltage V_1 is either lower than or equal to

the predetermined voltage V_2, and conversely, outputs high signal from the output terminal to the LSI circuit 26 if the characteristic voltage V_1 is higher than the predetermined voltage V_2. The operation of the LSI circuit 26 is controlled by the low and high signal from the distortion sensor 25. The LSI circuit 26 is thus specified to operate only when it receives low signal.

The step of mounting the chip 2 on the board 3 in the manufacture of the semiconductor device 1 of Figure 1(a) may be alternatively described as following.

First, the board 3 is fabricated including external output wiring for the wire section 6 so that the wiring matches in position the pad section 7 provided on the front of the chip 2 having a thickness of 200 μm or more. Meanwhile, a bump 4 is formed of gold on the pad section 7 on the front of the chip 2.

Then, as shown in Figure 4, after coating the board 3 with anisotropic conducting glue 5, the chip 2 is stacked on the board 3 so that the wire section 6 of the board 3 matches the bump 4 on the chip 2 in position. The chip 2 and the board 3 are compressed and secured to each other, while heating at about 200 °C. The glue 5 solidifies due to the heating, securing the chip 2 onto the board 3. In other words, the chip 2 is mounted in a flipped posture so as to be level on the board 3.

In addition, the scraping of the back 2a by means of the dicing blade 9 shown in Figure 4 to Figure 6 is preferably carried out in a specified direction (for example, in a direction normal to the paper showing Figure 5), that is, in a one direction so that the chip 2 readily deforms due to stress.

The chip 2 can entirely receive a predetermined stress as a result of the scrape processing by means of the dicing blade 9 as shown in Figure 4 to Figure 6, that is, as a result of the rough surface processing carried out on the back 2a entirely.

The semiconductor device 11 includes identical components as the semiconductor device 1 of the first embodiment, except the chip.

The chip 12 described in the second embodiment only needs to receive stress by processing at least a part of its back 12a. Therefore, if the processing is to be carried out by at least one method selected from the group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection, at least a part of the back 12a of the chip 12 needs to be processed. The chip 12 only needs to be specified so that at least a part of the chip 12 deforms, and more preferably at least a part of the transistor section 21 deforms convexly or concavely, due to stress

when detached from the board 3.

The semiconductor device 1 (11) of the first (second) embodiment is arranged so that the chip 2 (12) is secured level onto the board 3 (for example, with the chip being flipped) and operates normally only when it is level. Consequently, the chip 2 (12), when detached from the board 3 and is deformed, causes a change in an electrical or other property of, for example, the transistor section 21 and fails to operate normally. Thus, the chip 2 (12) is protected from analysis of the integrated circuit, and the secret information on the chip 2 (12) is safely concealed.

The chip 31 is secured onto the die pad (board) 32 interposed by the silver paste 33. The pad section 35 formed on the front of the chip 31 is electrically connected to the lead wire 36 via the gold wire 34. Therefore, the semiconductor device 30 has a structure of a wire bonding type. The back 31a of the chip 31 partially receives stress as a result of predetermined processing in such a fashion that the chip 31 deforms when the chip 31 is removed from the package 37, that is, when the chip 31 is detached from the die pad 32.

Similarly to the chip 2 of the first embodiment, the chip 31 includes a transistor section where transistors are provided at high density, a sensor section where

detector means is provided together with a comparator and other components to detect an electrical property of the transistors, and an LSI circuit section where circuitry including an IC or LSI circuit is provided. In the present embodiment, the chip 31 has thickness of 200 μm or more and partially thinned down to 50 μm or less and more preferably to a range of 30 μm to 50 μm. Therefore, the chip 31 readily deforms when detached from the die pad 32 due to stress applied to a part of the back 31a which is the processed part.

A part of the die pad 32 is omitted to make a hollow space. Consequently, the die pad 32 has a hollow section 32a to allow internal access during the processing carried out in a later step on at least a part of the back 31a of the chip 31.

Further, it is a fact confirmed by the data shown in Figures 17 and 18 that polishing (scraping) results in the formation of a stressed layer on the wafer (chip) and causes the wafer to warp.

The back of the polished wafer bears scratches from the polishing. Damaged semiconductor base material (typically, silicon) has its crystalline structure disrupted. Silicon can retain its normal state as long as crystals are interconnected orderly. But in damaged silicon, the orderly crystalline structure is disrupted

and broken with the crystal connections cut off. This disrupted part presumably becomes a stressed layer.

The present invention may be described as follows, by way of the first to sixth semiconductor devices and the first to third methods of manufacturing a semiconductor device. The first semiconductor device is a semiconductor device, in which a semiconductor element with an integrated circuit is secured to a board, and is arranged so that the semiconductor element is secured level and specified to operate normally only when the semiconductor element is level.

According to the arrangement, the semiconductor element is specified to operate normally only when it is level. Therefore, if the semiconductor element is no longer capable of sustaining its level shape as a result of, for example, detachment of the semiconductor element from the board, the semiconductor element does not operate normally due to a resultant change and the like in its electrical properties. This ensures that any analysis is prohibited from being conducted on the integrated circuit on the semiconductor element. Thus, secrets can be concealed safely about the semiconductor element.

The second semiconductor device is arranged so that, in the first semiconductor device, the semiconductor

element is of a flipped-chip mounting type.

According to the arrangement, to conduct analysis on the integrated circuit on the semiconductor element, the semiconductor element must be detached from the board. However, the semiconductor element, once detached from the board, is no longer capable of sustaining its level shape and fails to operate normally due to a resultant change in its electrical properties. Thus, secrets can be concealed safely about the semiconductor element.

The third semiconductor device is arranged so that in either one of the first and second semiconductor devices, the semiconductor element receives such stress as a result of processing at least a part of a back thereof that when the semiconductor element is detached from the board, the semiconductor element at least partially deforms due to the stress.

According to the arrangement, the semiconductor element is specified to at least partially deforms due to stress when detached from the board. Thus, a change occurs to an electrical property, and secrets can be concealed more safely.

The fourth semiconductor device is arranged so that in any one of the first to third semiconductor devices, the semiconductor element has a thickness of 50 μm or less where the semiconductor element is processed.

According to the arrangement, the semiconductor element, having a typical thickness of 200 μm or more, is fabricated so that when the semiconductor element is detached from the board, the processed, and thereby thinned down part more readily deforms due to stress. Thus, secrets can be concealed more safely.

The fifth semiconductor device is arranged so that in the first to fourth semiconductor devices, the semiconductor element is specified to include a transistor section where transistors are provided at high density, the transistor section at least partially deforming convexly or concavely due to the stress.

According to the arrangement, the semiconductor element is specified so that when the semiconductor element is detached from the board, the transistor section at least partially deforms convexly or concavely due to stress. Thus, a change occurs to an electrical property, and secrets can be concealed more safely.

The sixth semiconductor device is arranged so that in any one of the first to fifth semiconductor devices, the semiconductor element includes detector means for detecting an electrical property developing in a level part only when the level part is level, so as to control operation of the integrated circuit.

According to the arrangement, the semiconductor

element, if the semiconductor element is no longer capable of sustaining its level shape as a result of detachment from the board, a change occurs to its electrical properties. With the detector means detecting the change occurring to the electrical properties and thereby stopping the control of the operation of the integrated circuit, the semiconductor element fails to operate normally. This further ensures that any analysis is prohibited from being conducted on the integrated circuit on the semiconductor element. Thus, secrets can be concealed more safely.

The first method of manufacturing a semiconductor device includes, after securing a semiconductor element with an integrated circuit to a board so as to be level, the step of processing at least a part of a back of the semiconductor element to develop such stress that when the semiconductor element is detached from the board, at least a part thereof deforms.

According to the arrangement, the semiconductor element is given such stress that when the semiconductor element is detached from the board, at least a part thereof deforms. Therefore, if the semiconductor element is detached from the board and can no longer sustain its level shape, the semiconductor element does not operate normally due to a resultant change and the like in its

electrical properties. This ensures that any analysis is prohibited from being conducted on the integrated circuit on the semiconductor element. Thus, a semiconductor device can be manufactured in which secrets can be concealed safely about the semiconductor element.

The second method of manufacturing a semiconductor device is arranged so that in the first method of manufacturing a semiconductor device, the processing step is specified to be carried out by at least one technique selected from the group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection.

According to the method, the semiconductor element is given stress using an easy, convenient technique. Thus, a semiconductor device can be readily manufactured in which secrets can be concealed safely.

The third method of manufacturing a semiconductor device is arranged so that in either one of the first and second methods of manufacturing a semiconductor device, the semiconductor element is fabricated to have a thickness of 50 μm or less where the semiconductor element is processed.

According to the method, the semiconductor element, having a typical thickness of 200 μm or more, is fabricated so that the processed, and thereby thinned

down part more readily deforms due to stress. Thus, a semiconductor device can be readily manufactured in which secrets can be concealed more safely.

The invention being thus described, it will be obvious that the same may be varied in many ways. Such variations are not to be regarded as a departure from the spirit and scope of the invention, and all such modifications as would be obvious to one skilled in the art intended to be included within the scope of the following claims.